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April 1999

FDS6961A Dual N-Channel Logic Level PowerTrench[™] MOSFET

General Description

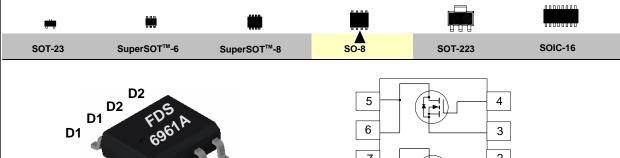
FAIRCHILD

These N-Channel Logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

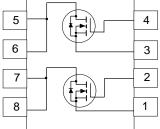
Features

- $\begin{array}{c|c} \bullet & 3.5 \text{ A}, \ 30 \ \text{V}. \ \text{R}_{\text{DS(ON)}} = 0.090 \ \Omega & @ \ \text{V}_{\text{GS}} = 10 \ \text{V} \\ & \text{R}_{\text{DS(ON)}} = 0.140 \ \Omega & @ \ \text{V}_{\text{GS}} = 4.5 \ \text{V}. \end{array}$
- Fast switching speed.
- Low gate charge (2.1nC typical).
- High performance trench technology for extremely low $\mathsf{R}_{\mathsf{DS}(\mathsf{ON})}.$
- High power and current handling capability.



G2 S2





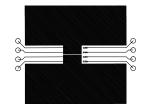
Absolute Maximum Ratings $T_a = 25^{\circ}C$ unless other wise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	30	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current - Continuous (Note 1a)	3.5	А
	- Pulsed	14	
P _D	Power Dissipation for Single Operation (Note 1)	2	W
	Power Dissipation for Single Operation (Note 1a)	1.6	
	(Note 1b)	1	
	(Note 1c)	0.9	
T_,,T _{stg}	Operating and Storage Temperature Range	-55 to 150	°C
THERMA	L CHARACTERISTICS		
R _{eja}	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	°C/W
R _{euc}	Thermal Resistance, Junction-to-Case (Note 1)	40	°C/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHAR	ACTERISTICS		•	•	•	•
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$	30			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25 °C		25		mV/ºC
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 V, V_{GS} = 0 V$			1	μA
		$T_{J} = 55^{\circ}C$			10	μA
	Gate - Body Leakage, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			-100	nA
	CTERISTICS (Note 2)	·				
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.8	3	V
$\Delta V_{GS(th)} / \Delta T_J$	Gate Threshold Voltage Temp. Coefficient	$I_{\rm D}$ = 250 µA, Referenced to 25 °C		-5		mV/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 3.5 \text{ A}$		0.076	0.09	Ω
. ,		T, =125°C		0.11	0.155	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 2.8 \text{ A}$		0.107	0.14	
I _{D(ON)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	14			Α
9 _{FS}	Forward Transconductance	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 3.5 \text{ A}$		6		S
Dynamic (HARACTERISTICS					
C _{iss}	Input Capacitance	$V_{DS} = 15 V, V_{GS} = 0 V,$ f = 1.0 MHz		220		pF
C _{oss}	Output Capacitance			50		pF
C _{rss}	Reverse Transfer Capacitance			20		pF
SWITCHING	CHARACTERISTICS (Note 2)		-	•	•	
t _{D(on)}	Turn - On Delay Time	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 1 \text{ A}$		3	6	ns
t,	Turn - On Rise Time	$V_{GS} = 10 \text{ V}$, $R_{GEN} = 6 \Omega$		11	22	ns
t _{D(off)}	Turn - Off Delay Time			7	14	ns
t _r	Turn - Off Fall Time			3	6	ns
Q _g	Total Gate Charge	$V_{\rm DS} = 15 \text{ V}, \ \text{I}_{\rm D} = 3.5 \text{ A},$		2.1	4	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 5 V$		0.8		nC
Q_{gd}	Gate-Drain Charge			0.7		nC
DRAIN-SOU	RCE DIODE CHARACTERISTICS AND MAXIMU	JM RATINGS				
s	Maximum Continuous Drain-Source Diode Fo	ontinuous Drain-Source Diode Forward Current			1.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 1.3 A$ (Note 2)		0.73	1.2	V

1. R_{gut} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{gut} is guaranteed by design while R_{gut} is determined by the user's board design.

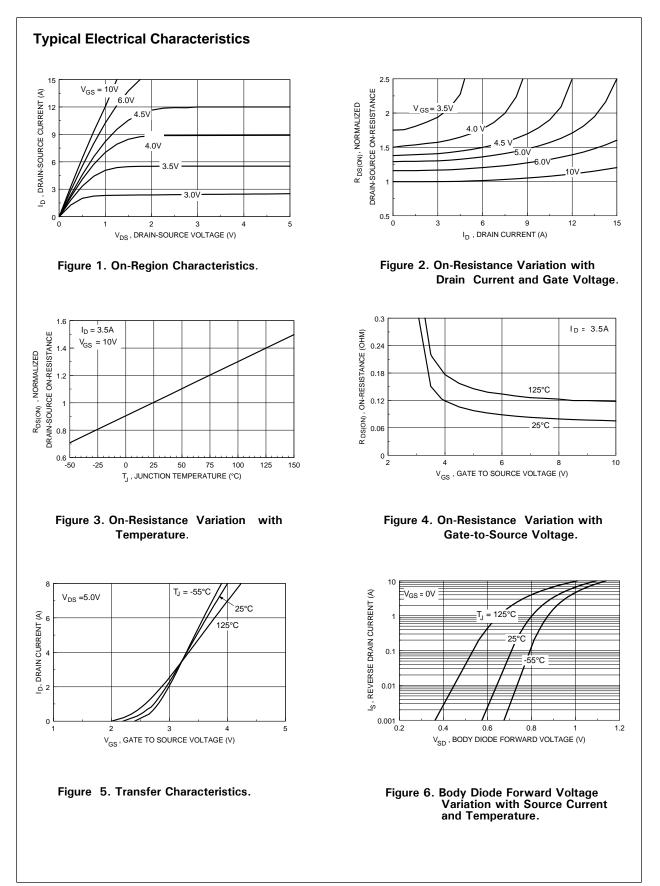


a. 78°C/W on a 0.5 in² pad of 2oz copper.

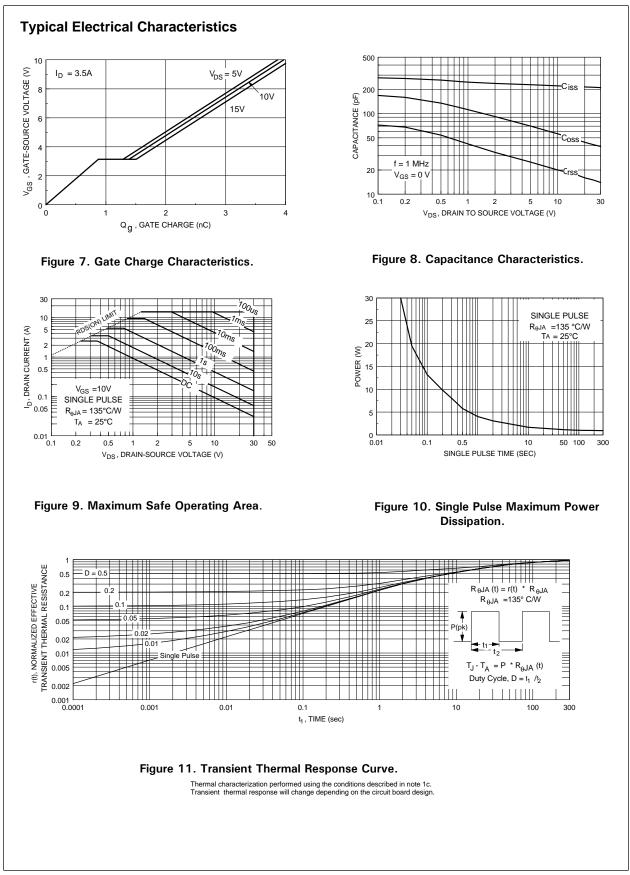
b. 125°C/W on a 0.02 in² pad of 20z copper.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.



FDS6961A Rev.C



FDS6961A Rev.C

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